

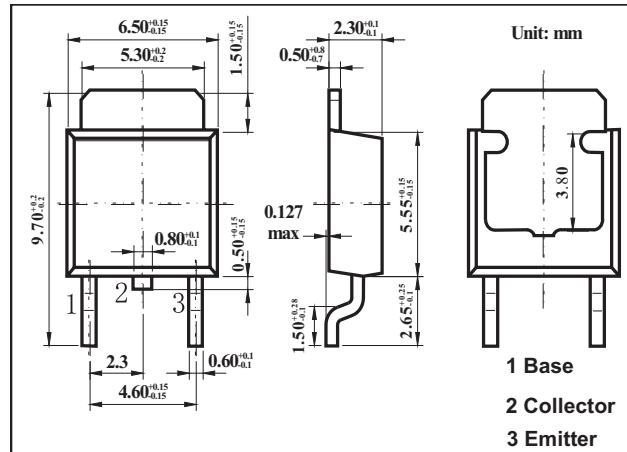
TO-252 Plastic-Encapsulate Transistors

FEATURES

- PNP TRANSISTORS
- Collector-Base Voltage: VCBO=-40V
- Low Speed Switching

MECHANICAL DATA

- Case style:TO-252 molded plastic
- Mounting position:any



MAXIMUM RATINGS AND CHARACTERISTICS

@ 25°C Ambient Temperature (unless otherwise noted)

Parameter	Symbol	Value	Unit
Collector-Base Voltage	V _{CBO}	-40	V
Collector-Emitter Voltage	V _{CEO}	-30	V
Emitter-Base Voltage	V _{EBO}	-6	V
Collector Current -Continuous	I _C	-3	A
Collector Power Dissipation	P _C	1.25	W
Thermal Resistance from Junction to Ambient	R _{θJA}	100	°C/W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 ~ +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	I _C =-100μA , I _E =0	-40			V
Collector-emitter breakdown voltage	V _{(BR)CEO}	I _C = -10mA , I _B =0	-30			V
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E = -100μA,I _C =0	-6			V
Collector cut-off current	I _{CBO}	V _{CB} = -40V,I _E =0			-1	μA
Collector cut-off current	I _{CEO}	V _{CE} =-30V, I _B =0			-10	μA
Emitter cut-off current	I _{EBO}	V _{EB} =-6V, I _C =0			-1	μA
DC current gain	h _{FE}	V _{CE} = -2V, I _C = -1A	60		400	
Collector-emitter saturation voltage	V _{CE(sat)}	I _C =-2A, I _B = -0.2A			-0.5	V
Base-emitter saturation voltage	V _{BE(sat)}	I _C =-2A, I _B = -0.2A			-1.5	V
Transition frequency	f _T	V _{CE} = -5V, I _C =-0.1A f =10MHz	50	80		MHz